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November 2013

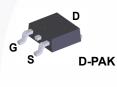
FQD10N20C / FQU10N20C N-Channel QFET[®] MOSFET 200 V, 7.8 A, 360 mΩ

Features

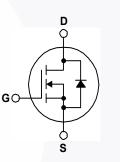
- + 7.8 A, 200 V, $R_{DS(on)}$ = 360 m Ω (Max.) @ V_{GS} = 10 V, I_{D} = 3.9 A
- Low Gate Charge (Typ. 20 nC)
- Low Crss (Typ. 40.5 pF)
- 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQD10N20CTM / FQU10N20CTU	Unit
V _{DSS}	Drain-Source Voltage		200	V
	Drain Current - Continuous ($T_C = 25^{\circ}C$)		7.8	А
D	- Continuous (T _C = 100°C)		5.0	А
I _{DM}	Drain Current - Pulsed	(Note 1)	31.2	А
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	210	mJ
I _{AR}	Avalanche Current	(Note 1)	7.8	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns
D_	Power Dissipation (T _C = 25°C)		50	W
P _D	- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
Τ _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C
			500	

Thermal Characteristics

Symbol	Parameter	FQD10N20CTM / FQU10N20CTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	0/10

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Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQD10N20C	FQD10N20CTM	D-PAK	330 mm	16 mm	2500 units
FQU10N20C	FQU10N20CTU	I-PAK	Tube	N/A	70 units

Electrical Characteristics $T_{C} = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	200			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		0.28		V/°(
		V _{DS} = 200 V, V _{GS} = 0 V			10	μA
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 160 V, T _C = 125°C			100	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.9 A	-	0.29	0.36	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 3.9 A		5.6		S
Dynamic Characteristics C _{iss} Input Capacitance V _{DS} = 25 V, V _{GS} = 0 V,			395	510	pF	
C _{oss}	Output Capacitance	f = 1.0 MHz		97	125	pF
C _{rss}	Reverse Transfer Capacitance			40.5	53	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100 V, I _D = 9.5 A,		11	30	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		92	190	ns
t _{d(off)}	Turn-Off Delay Time	5	/	70	150	ns
t _f	Turn-Off Fall Time	(Note 4)	-	72	160	ns
Qg	Total Gate Charge	V _{DS} = 160 V, I _D = 9.5 A,	-	20	26	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		3.1		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	10.5		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Dic			/	7.8	A
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			31.2	A

IS	Maximum Continuous Drain-Source Diode Forward Current		 	7.8	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		 1	31.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 7.8 A	 	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 9.5 A,	 158	1	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/µs	 0.97	1	μC

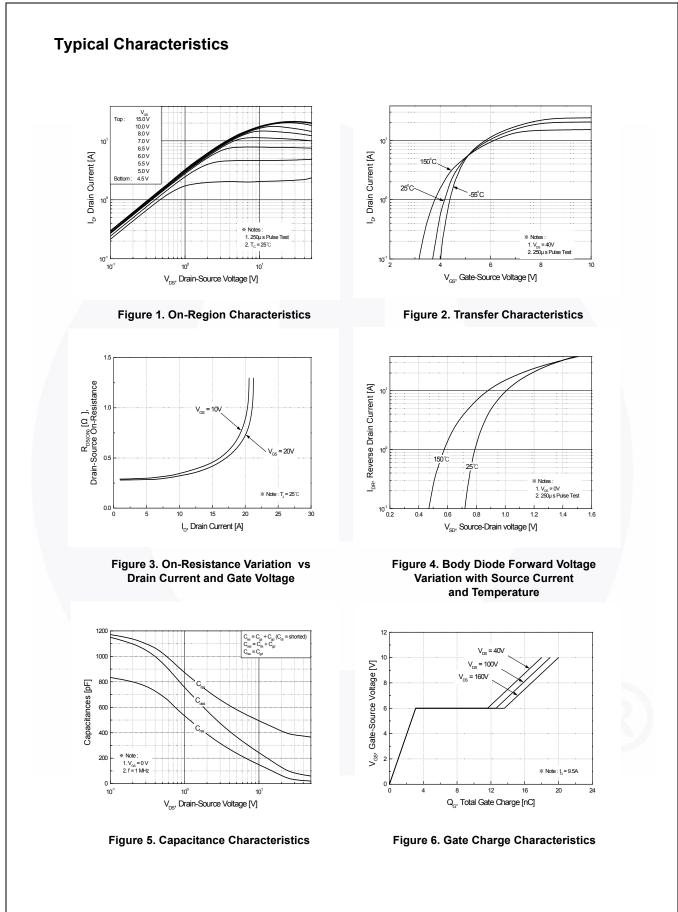
NOTES:

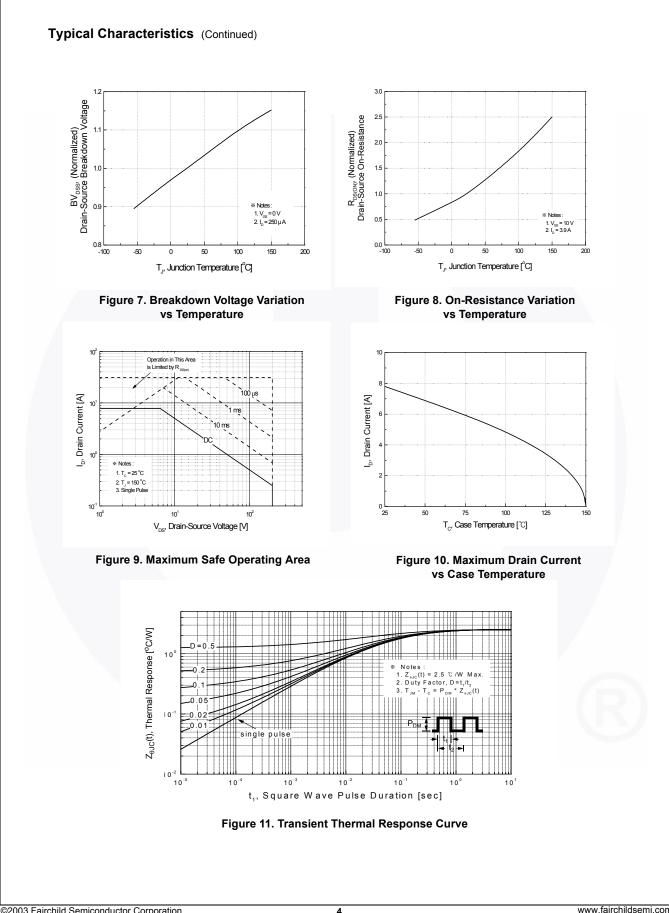
1. Repetitive Rating : Pulse width limited by maximum junction temperature.

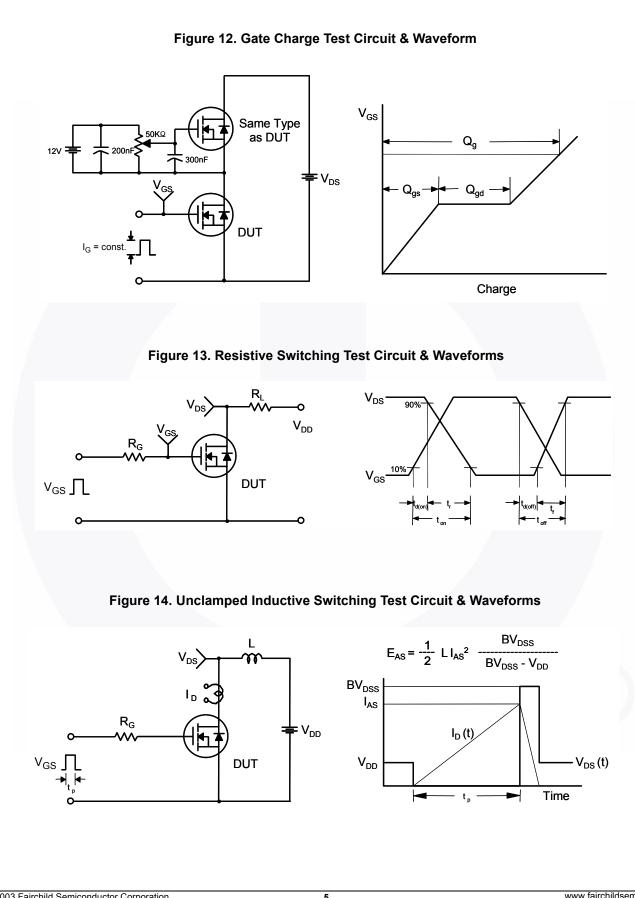
2. L = 5.2 mH, I_{AS} = 7.8 A, V_{DD} = 50 V, R_G = 25 $\Omega,$ starting $\mbox{ T}_{J}$ = 25°C.

3. I_{SD} \leq 9.5 A, di/dt \leq 300 A/µs, V_{DD} \leq BV_{DSS,} starting ~T_J = 25°C.

4. Essentially independent of operating temperature.

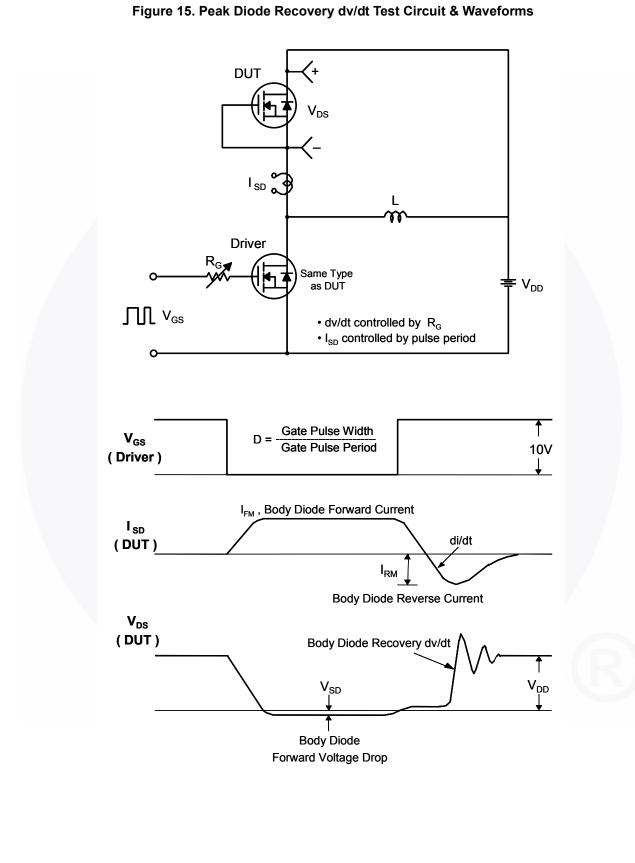


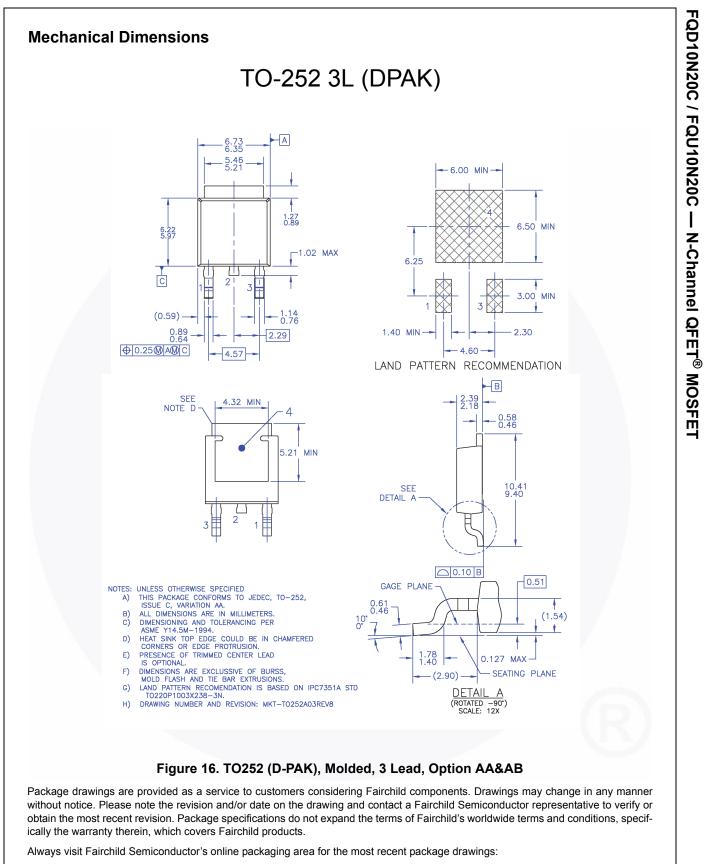




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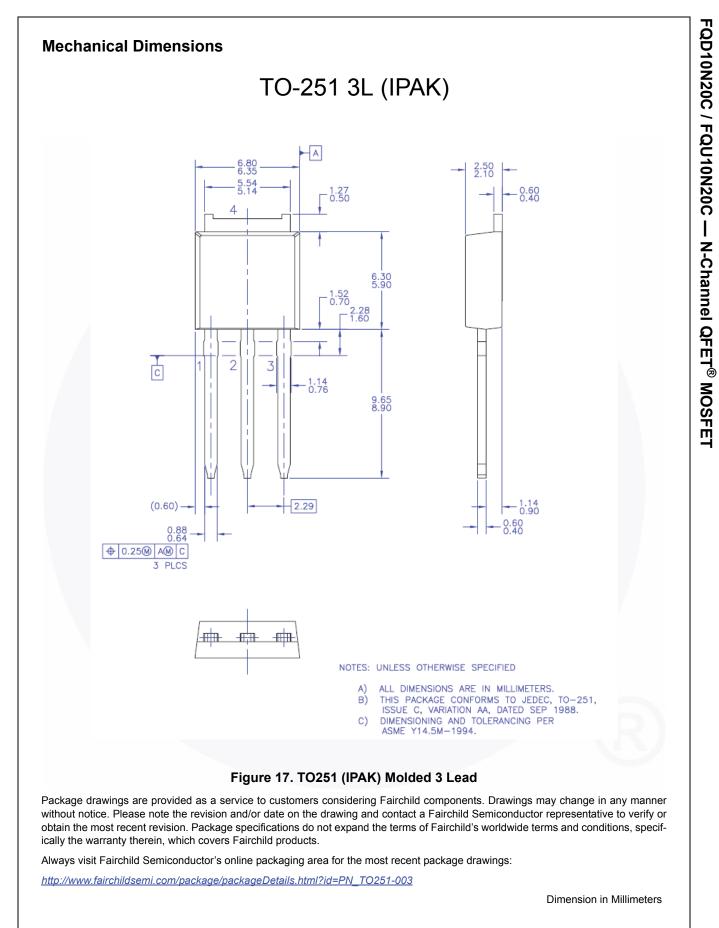
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Dimension in Millimeters





SEMICONDUCTOR

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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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FQD10N20C / FQU10N20C — N-Channel QFET[®] MOSFET

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